

DATA SHEET

BAS116/BAW156/BAV170/BAV199

SURFACE MOUNT, LOW LEAKAGE SWITCHING DIODES

| | | | |
|----------------|------------------|--------------|------------------|
| VOLTAGE | 100 Volts | POWER | 250mWatts |
|----------------|------------------|--------------|------------------|

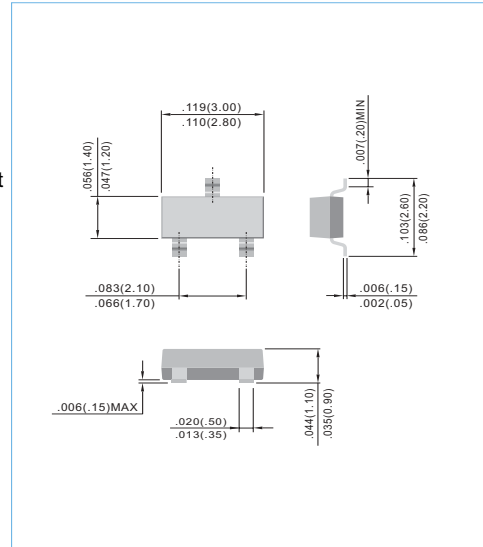
SOT- 23 Unit: inch (mm)

FEATURES

- Surface mount package ideally suited for automatic insertion.
- Very low leakage current. 2pA typical at VR=75V.
- Low capacitance. 2pF max at VR=0V, f=1MHz
- Pb free product are available : 99% Sn above can meet Rohs environment substance directive request

MECHANICAL DATA

- Case: SOT-23 plastic
- Terminals: Solderable per MIL-STD-202G, Method 208
- Approx weight: 0.008 gram
- Marking: BAS116: P1,BAW156:P4,BAV170:P3,BAV199:P2



ABSOLUTE RATINGS (each diode)

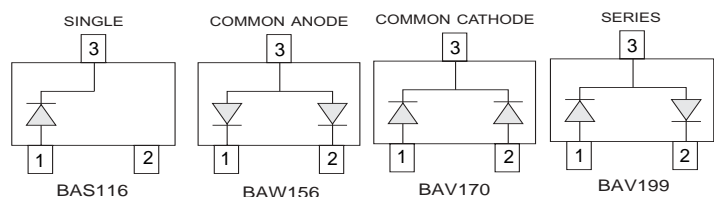
| PARAMETER | Sym bol | Value | Units |
|---|-----------|-------|-------|
| Reverse Voltage | V_R | 75 | V |
| Peak Reverse Voltage | V_{RM} | 100 | V |
| Continuous Forward Current | I_F | 0.2 | A |
| Non-repetitive Peak Forward Surge Current at $t=1.0\mu s$ | I_{FSM} | 2.0 | A |

THERMAL CHARACTERISTICS

| PARAMETER | Sym bol | Value | Units |
|--|-----------------|------------|---------------|
| Power Dissipation (Note 1) | P_{TOT} | 250 | mW |
| Thermal Resistance, Junction to Ambient (Note 1) | $R_{\theta JA}$ | 500 | $^{\circ}C/W$ |
| Junction Temperature | T_J | -55 to 150 | $^{\circ}C$ |
| Storage Temperature | T_{STG} | -55 to 150 | $^{\circ}C$ |

NOTE:

1. FR-5 Board = 1.0 x 0.75 x 0.062 in.



ELECTRICAL CHARACTERISTICS (each diode) ($T_A=25^{\circ}\text{C}$, unless otherwise noted)

| PARAMETER | Sym bol | Test Condition | M IN . | TYP . | M AX . | Units |
|---------------------------|------------|--|--------|--------------|---------------------------|---------------|
| Reverse Breakdown Voltage | $V_{(BR)}$ | $I_R=100\text{ }\mu\text{A}$ | 75 | | | V |
| Reverse Current | I_R | $V_R=75\text{ V}$ $V_R=75\text{ V}, T_J=150^{\circ}\text{C}$ | | 0.002 8.0 | 5 80 | nA |
| Forward Voltage | V_F | $I_F=1\text{ mA}$ $I_F=10\text{ mA}$ $I_F=50\text{ mA}$ $I_F=150\text{ mA}$ | | | 0.9 1.0 1.1 1.25 | V |
| Total Capacitance | C_T | $V_R=0\text{ V}, f=1\text{ MHz}$ | | | 2.0 | pF |
| Reverse Recovery Time | T_{RR} | $I_F=I_R=10\text{ mA}, R_L=100\Omega$ | | | 3.0 | μs |

CHARACTERISTIC CURVES (each diode)

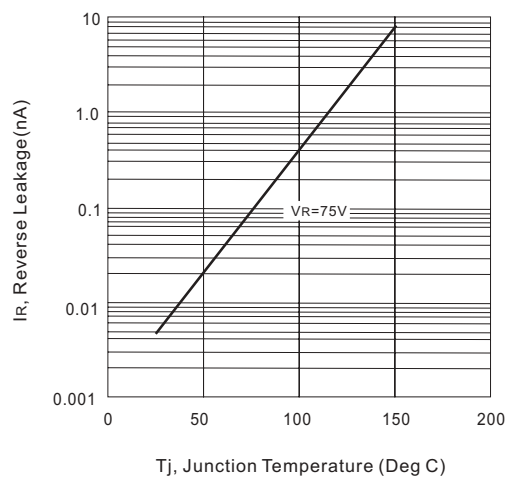


Fig. 1-Reverse Leakage vs. Junction Temperature

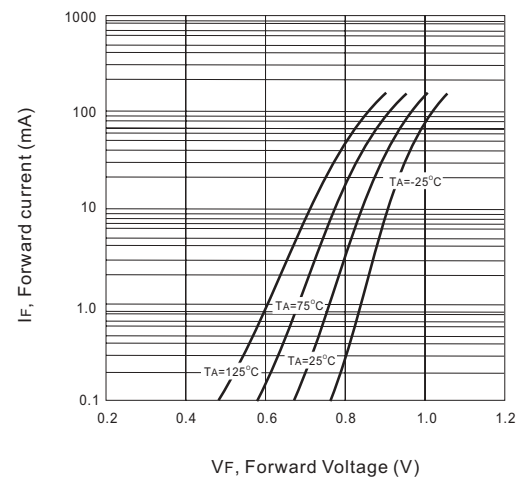


Fig. 2-Forward Current vs. Forward Voltage

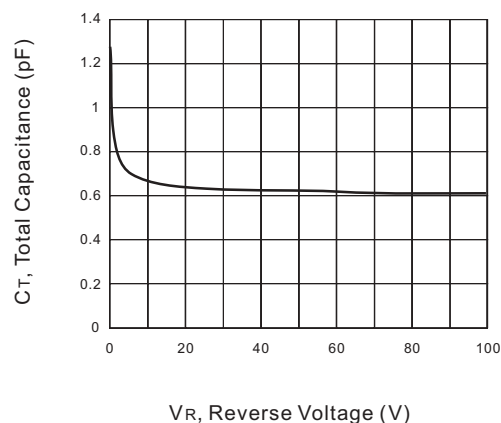
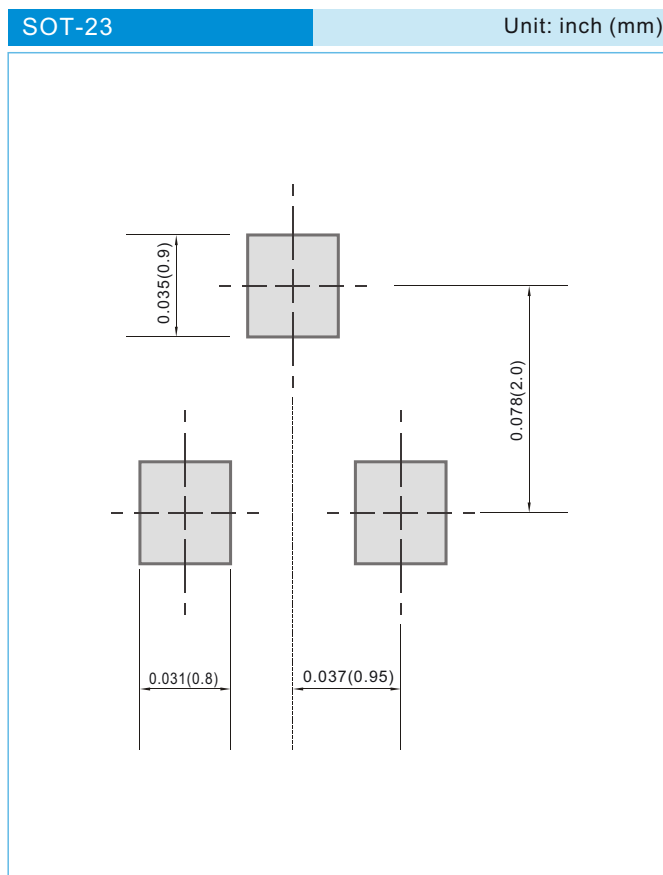


Fig. 3- Total capacitance vs. Reverse Voltage

MOUNTING PAD LAYOUT



ORDER INFORMATION

- Packing information
 - T/R - 12K per 13" plastic Reel
 - T/R - 3.0K per 7" plastic Reel

LEGAL STATEMENT

IMPORTANT NOTICE

This information is intended to unambiguously characterize the product in order to facilitate the customer's evaluation of the device in the application. The information will help the customer's technical experts determine that the device is compatible and interchangeable with similar devices made by other vendors. The information in this data sheet is believed to be reliable and accurate. The specifications and information herein are subject to change without notice. New products and improvements in products and product characterization are constantly in process. Therefore, the factory should be consulted for the most recent information and for any special characteristics not described or specified.

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